

Substitute Form PTO-1449
(Modified)U.S. Department of Commerce
Patent and Trademark OfficeAttorney's Docket No.
07977-004002Application No.
~~New Continuation~~
Application 10 60226 C**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

Applicant
Naoto Kusumoto et al.Filing Date
June 25, 2003Group Art Unit
2828**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>Drfa</i>	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	AE	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			
	AG	5,365,875	11/1994	Asai et al.			
	AH	5,424,244	6/13/95	Zhang, et al.			
	AI	5,432,122	07/1995	Chae			
	AJ	5,477,073	12/1995	Wakai et al.			
	AK	5,496,768	03/1996	Kudo			
	AL	5,561,081	02/1994	Takenouchi et al.			
	AM	5,591,668	01/1997	Maegawa et al.			
	AN	5,643,801	7/1/97	Ishihara, et al.			
	AO	5,795,795	8/18/98	Kousai, et al.			
	AP	5,849,043	12/15/98	Zhang, et al.			
	AQ	5,891,764	4/6/99	Ishihara, et al.			
	AR	5,897,799	4/27/99	Yamazaki et al			
	AS	6,143,661	11/7/2000	Kousai, et al.			
<i>Drfa</i>	AT	6,358,784	03/19/2002	Zhang, et al			

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<i>Drfa</i>	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
<i>Drfa</i>	AX	3-286518	12/1991	Japan				

Examiner Signature

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Attorney's Docket No.
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Application No.
~~New Continuation~~
 Application 10-602762

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 (Use several sheets if necessary)

Applicant
 Naoto Kusumoto et al.

Filing Date
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Group Art Unit
 2828


(37 C.F.R. § 1.98(b))

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
DPN	AY	4-307727	10/1992	Japan				

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
DPN	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; <i>MRS Symp. Proc.</i> 343; pp. 709; 1994
	AAA	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> 37-38; pp. 299-304; 1994
	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; <i>Appl. Surf. Sci.</i> 36; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; <i>IEEE IEDM</i> ; pp. 829-832; 1995
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	AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; <i>Jpn. J. Appl. Phys</i> 33(10B); p. L1438; October 1994
	AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", <i>IEEE Transactions on Electron Devices</i> , Vol. 42, No. 2, pp. 251-257
	AHH	Kuriyama et al.; "Improving...ELA method for giant microelectronics"; <i>Jpn. J. Appl. Phys.</i> 31(12B); p. 4550; December 1992
	AII	Kuriyama et al.; "Lateral growth of Poly-Si films...by ELA..."; <i>Jpn. J. Appl. Phys.</i> 32(12B); p. 6190; December 1993
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DPN	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; <i>Optical Eng.</i> 31(2); p. 245; February 1992

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Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. New Continuation Application 0602762
	Applicant Naoto Kusumoto et al.		
	Filing Date June 25, 2003	Group Art Unit 2828	

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DFA	AA	3,585,088	06/1971	Scwuttke et al.			
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DFA	AT	6,358,784	03/19/2002	Zhang, et al.			

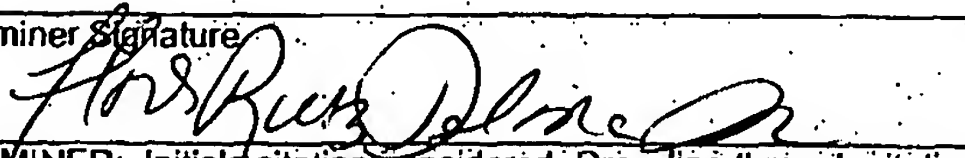
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Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))				Applicant Nanto Kusumoto et al.			
				Filing Date June 25, 2003		Group Art Unit 2828	
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DM	AY	4-307727	10/1992	Japan			

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DM	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; <i>MRS Symp. Proc.</i> 343; pp. 709; 1994
	AAA	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> ; pp. 37-38; 1994
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	AJJ	Okumura et al.; "Excimer laser annealed poly-Si TFT technologies"; <i>MRS Symp. Proc.</i> 377; p. 877; April 1995
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Sheet 1 of 1

Substitute Form PTO-1449

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Patent and Trademark Office

Attorney's Docket No.

07977-004002

Application No.

10/602,762

**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant

Naoto Kusumoto et al.

Filing Date

June 25, 2003

Group Art Unit

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U.S. Patent Documents

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	AA						
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	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

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	AJ							
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DPN	AO	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> , Vol. 37-38; pp. 209-304; 1994

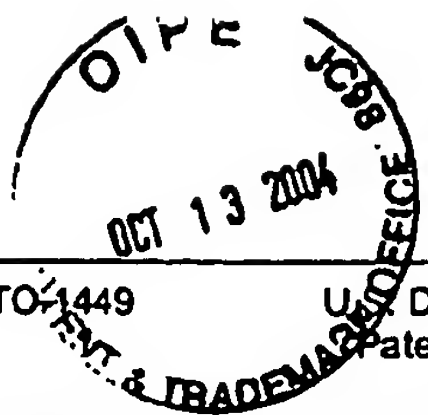
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Substitute Disclosure Form (PTO-1449)

Sheet 1 of 1

Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. 10/602,762
	Applicant Naoto Kusumoto et al.		
	Filing Date June 25, 2003	Group Art Unit 2828	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>DAU</i>	AA	2003/0015133	01/23/2003	ZHANG et al.			08/22/2002
	AB	2003/0207524	11/06/2003	ZHANG et al.			06/04/2003
	AC	5,352,291	10/04/1994	ZHANG et al.			08/11/1993
	AD	5,578,520	11/26/1996	ZHANG et al.			07/15/1994
	AE	5,766,344	06/16/1998	ZHANG et al.			05/26/1995
	AF	5,861,337	01/19/1999	ZHANG et al.			06/02/1995
	AG	6,174,374	01/16/2001	ZHANG et al.			09/26/1996
	AH	6,494,162	12/17/2002	ZHANG et al.			10/25/2000
	AI	6,576,534	06/10/2003	ZHANG et al.			02/10/1998
	AJ	6,770,143	08/03/2004	ZHANG et al.			08/22/2002
<i>SM</i>	AK						

Foreign Patent Documents or Published Foreign Patent Applications								
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							Yes	No
<i>DAU</i>	AL	JP05-182923	23 JUL 1993	JAPAN			Abstract	
<i>DAU</i>	AM	JP05-198507	06 AUG 1993	JAPAN			Abstract	
	AN							
	AO							
	AP							

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U.S. Patent Documents							
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<i>Dra</i>	AA	5,569,610	10/29/1996	Zhang et al.			03/08/1994
<i>Dra</i>	AB	5,614,733	03/25/1997	Zhang et al.			12/12/1994
<i>Dra</i>	AC	5,783,468	07/21/1998	Zhang et al.			04/10/1996
	AD						
	AE						
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							Yes	No
<i>Dra</i>	AL	02-224346	09/06/1990	JAPAN			ABS	
<i>Dra</i>	AM	06-318701	11/15/1994	JAPAN			ABS	
<i>Dra</i>	AN	08-051074	02/20/1996	JAPAN			ABS	
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